L Number	Hits	Search Text	DB	Time stamp
-	132510	fin or fin\$1fet or fin\$1mosfet or fin\$1mos	USPAT;	2004/10/03 10:20
		or fin\$1mis or fin\$1misfet	US-PGPUB;	
			EPO; JPO; DERWENT;	
			IBM TDB	
_	589910	capacitor	USPAT;	2004/10/03 10:20
			US-PGPUB;	
			EPO; JPO;	
			DERWENT; IBM TDB	
_	127163	(fin or fin\$1fet or fin\$1mosfet or	USPAT;	2004/10/03 10:20
		fin\$1mos or fin\$1mis or fin\$1misfet) not	US-PGPUB;	
		capacitor	EPO; JPO;	
			DERWENT; IBM TDB	
_	2941773	semiconductor or silicon or si	USPAT;	2004/10/03 10:21
	23.27.0		US-PGPUB;	
			EPO; JPO;	
			DERWENT;	•
_	16704	((fin or fin\$lfet or fin\$1mosfet or	IBM_TDB USPAT;	2004/10/03 10:22
	10704	fin\$1mos or fin\$1mis or fin\$1misfet) not	US-PGPUB;	2004/10/03 10.22
		capacitor) and (semiconductor or silicon	EPO; JPO;	
1		or si)	DERWENT;	
	000001		IBM_TDB USPAT;	2004/10/03 10:22
-	888901	gate	USPAT; US-PGPUB;	2004/10/03 10:22
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	0004/10/00 10 00
-	1545	(((fin or fin\$1fet or fin\$1mosfet or fin\$1mos or fin\$1mis or fin\$1misfet) not	USPĀT; US-PGPUB;	2004/10/03 10:22
		capacitor) and (semiconductor or silicon	EPO; JPO;	
		or si)) and gate	DERWENT;	
			IBM_TDB	
-	286790	drain and source	USPAT; US-PGPUB;	2004/10/03 10:26
			EPO; JPO;	
-	0		DERWENT;	
			IBM_TDB	
-	480		USPAT;	2004/10/03 12:12
		fin\$1mos or fin\$1mis or fin\$1misfet) not capacitor) and (semiconductor or silicon	US-PGPUB; EPO; JPO;	
		or si)) and gate) and (drain and source)	DERWENT;	
			IBM_TDB	
-	3803641	apparatus	USPAT;	2004/10/03 11:53
			US-PGPUB; EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	94205		USPAT;	2004/10/03 11:53
		fin\$1mos or fin\$1mis or fin\$1misfet) not capacitor) not apparatus	US-PGPUB; EPO; JPO;	
		oupdoicol, not apparatus	DERWENT;	
			IBM_TDB	
-	218	1 , , , ,	USPAT;	2004/10/03 11:59
		fin\$1mos or fin\$1mis or fin\$1misfet) not capacitor) not apparatus) and	US-PGPUB; EPO; JPO;	
		(semiconductor or silicon or si) and	DERWENT;	
		drain) not (((((fin or fin\$1fet or	IBM_TDB	
		fin\$1mosfet or fin\$1mos or fin\$1mis or		
		fin\$1misfet) not capacitor) and (semiconductor or silicon or si)) and		
		(semiconductor or silicon or si)) and gate) and (drain and source))	ĺ	
-	356098		USPAT;	2004/10/03 12:00
			US-PGPUB;	
}			EPO; JPO;	
			DERWENT; IBM TDB	
L			1 100	

	7035	(438/\$.ccls. or 257/\$.ccls.) and fin	USPAT; US-PGPUB; EPO; JPO;	2004/10/03 12:00
			DERWENT; IBM TDB	
-	5289	((438/\$.ccls. or 257/\$.ccls.) and fin) not capacitor	USPAT; US-PGPUB;	2004/10/03 12:00
			EPO; JPO; DERWENT;	
_	577944	mos\$1fet or mos or mis\$1fet or pmos or	IBM_TDB USPAT;	2004/10/03 12:03
		nmos or field adj5 transistor ig\$1fet or fet	US-PGPUB; EPO; JPO; DERWENT;	
_	524	(((438/\$.ccls. or 257/\$.ccls.) and fin)	IBM_TDB USPAT;	2004/10/03 12:03
		not capacitor) and (mos\$lfet or mos or mis\$lfet or pmos or nmos or field adj5 transistor ig\$lfet or fet)	US-PGPUB; EPO; JPO; DERWENT;	
		-	IBM_TDB	0004/10/00 10 00
-	310	((((438/\$.ccls. or 257/\$.ccls.) and fin) not capacitor) and (mos\$1fet or mos or	USPAT; US-PGPUB;	2004/10/03 12:03
		mis\$1fet or pmos or nmos or field adj5 transistor ig\$1fet or fet)) not (((((fin	EPO; JPO; DERWENT;	
		or fin\$1fet or fin\$1mosfet or fin\$1mos or fin\$1mis or fin\$1misfet) not capacitor)	IBM_TDB	
		and (semiconductor or silicon or si)) and		
_	2701		USPAT;	2004/10/03 12:16
		438/157.ccls. or 438/164.ccls. or 438/283.ccls. or 438/284.ccls.	US-PGPUB; EPO; JPO;	
			DERWENT; IBM TDB	
-	36	(438/149.ccls. or 438/151.ccls. or 438/157.ccls. or 438/164.ccls. or	USPĀT; US-PGPUB;	2004/10/03 12:16
		438/283.ccls. or 438/284.ccls.) and fin	EPO; JPO; DERWENT;	
			IBM_TDB	0004/10/00 10 45
_	226	fin\$1mos or fin\$1mis or fin\$1misfet) not	USPAT; US-PGPUB;	2004/10/03 12:45
		capacitor) and (semiconductor or silicon or si)) and gate) and (source\$ldrain or	EPO; JPO; DERWENT;	
_	56	s\$1d) ((((fin or fin\$1fet or fin\$1mosfet or	IBM_TDB USPAT;	2004/10/03 13:16
		fin\$1mos or fin\$1mis or fin\$1misfet) not capacitor) and (semiconductor or silicon	US-PGPUB; EPO; JPO;	
		or si)) and gate) and (source\$1drain or s\$1d)) not (((((fin or fin\$1fet or	DERWENT; IBM TDB	
		fin\$1mosfet or fin\$1mos or fin\$1mis or fin\$1misfet) not capacitor) and		
		(semiconductor or silicon or si)) and gate) and (drain and source))		
-	6	gate) and (drain and source)) ("6642090" or "6635909" or "6611029").pn.	USPAT;	2004/10/03 12:58
			US-PGPUB; EPO; JPO;	
			DERWENT; IBM_TDB	
-	0	10.src and 040869.ap	USPAT; US-PGPUB;	2004/10/03 12:59
			EPO; JPO; DERWENT;	
_	0	09.src and 040869.ap	IBM_TDB USPAT;	2004/10/03 12:59
		os.sic and ogoods.ap	US-PGPUB;	2004/10/03 12:39
			EPO; JPO; DERWENT;	
-	0	10.src and 040869.ap.	IBM_TDB USPAT;	2004/10/03 12:59
			US-PGPUB; EPO; JPO;	
			DERWENT; IBM TDB	
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-	5	("040869").ap.	USPAT;	2004/10/03 13:06
		•	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	5	041182.ap.	USPAT;	2004/10/03 13:07
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	6	274961.ap.	USPĀT;	2004/10/03 13:09
		•	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	3	310777.ap.	USPAT;	2004/10/03 13:09
			US-PGPUB;	
		•	EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	2	("20040075122").PN.	USPĀT;	2004/10/03 13:22
		(200400/3122 /	US-PGPUB;	2001,10,00 13.22
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	2	("20030227057").PN.	USPAT;	2004/10/03 13:23
		(20030227037).114.	US-PGPUB;	2001/10/03 13:23
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	4686	(257/347 or 257/368 or 257/401).ccls.	USPAT;	2004/10/05 12:14
	1000	(237/347 01 237/300 01 237/401/:0013:	US-PGPUB;	2004/10/05 12:14
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
	132617	fin	USPAT;	2004/10/05 12:14
_	13201/	1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1	US-PGPUB;	2004/10/03 12:14
			EPO; JPO;	
			DERWENT;	
			1	
	65	((257/347 or 257/368 or 257/401).ccls.)	IBM_TDB USPAT;	2004/10/05 12:15
_	65	and fin		2004/10/05 12:15
		and tin	US-PGPUB;	
1			EPO; JPO;	1
1			DERWENT;	
I	1	1	IBM TDB	1